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	Application No.	Applicant(s)	
Notice of Allewshills	10/712,236	CHEN ET AL.	
Notice of Allowability	Examiner	Art Unit	
	Shouxiang Hu	2811	
The MAILING DATE of this communication ap All claims being allowable, PROSECUTION ON THE MERITS herewith (or previously mailed), a Notice of Allowance (PTOL-8 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT of the Office or upon petition by the applicant. See 37 CFR 1.3 1. \(\infty\) This communication is responsive to the 04-18-2005 and	IS (OR REMAINS) CLOSED in the second of the	n this application. If not inclu unication will be mailed in du	ided e course. <b>THIS</b>
2. ⊠ The allowed claim(s) is/are <u>12-15 and 18</u> .			
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3. The drawings filed on 12 November 2003 are accepted	by the Examiner.		
4. Acknowledgment is made of a claim for foreign priority a) All b) Some* c) None of the:  1. Certified copies of the priority documents had 2. Certified copies of the priority documents had 3. Copies of the certified copies of the priority International Bureau (PCT Rule 17.2(a)).  * Certified copies not received:  Applicant has THREE MONTHS FROM THE "MAILING DAT noted below. Failure to timely comply will result in ABANDOI THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.  5. A SUBSTITUTE OATH OR DECLARATION must be sull INFORMAL PATENT APPLICATION (PTO-152) which comply including changes required by the Notice of Draftsperior (a) including changes required by the Notice of Draftsperior (b) including changes required by the attached Examin Paper No./Mail Date  Identifying indicia such as the application number (see 37 CFI each sheet. Replacement sheet(s) should be labeled as such in the decomplete of the d	ave been received.  ave been received in Application documents have been received.  E" of this communication to file NMENT of this application.  bmitted. Note the attached EX gives reason(s) why the oath or nust be submitted.  erson's Patent Drawing Reviewer's Amendment / Comment or the header according to 37 CF posit of BIOLOGICAL MAT	on No  d in this national stage applicate a reply complying with the reply complying complying the reply complying comp	requirements  NOTICE OF  he back) of
Attachment(s)  1. Notice of References Cited (PTO-892)  2. Notice of Draftperson's Patent Drawing Review (PTO-94)  3. Information Disclosure Statements (PTO-1449 or PTO/S) Paper No./Mail Date  4. Examiner's Comment Regarding Requirement for Depos of Biological Material	8) 6. Interview S Paper No. B/08), 7. Examiner's it 8. Examiner's 9. Other	Informal Patent Application (Postummary (PTO-413), /Mail Date 20050621. Amendment/Comment Statement of Reasons for A	·
		MARY EXAMINED	

## **EXAMINER'S AMENDMENT**

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Jiawei Huang (RN: 43,330) on June 20, 2005.

The application has been amended as follows:

## IN THE CLAIMS

Claims 1-11. (Cancelled)

Claim 12. (Currently Amended) A diode string structure having a starting end and a terminal end, comprising:

- a substrate of a first conductive type;
- a diode string having a starting end and a terminal end on the substrate;
- a first well region of a second conductive type located within the substrate;
- a first doped region of the second conductive type located within the first well region, wherein the first doped region is <u>heavily doped and forms</u> the starting end of the diode string structure and adjacent to the surface of the substrate, and the first doped region is coupled to a drain terminal; and

at least two diode structures located within the first well region, wherein one of the diode structures is a starting diode structure adjacent to the starting end of the diode string structure, one of the diode structure is an ending diode structure as <u>forming</u> the terminal end of the diode string <u>structure</u>, and each <u>of the</u> diode structures comprises:

a second well region with the first conductive type located within the first well region, wherein the second well region is not physically contacted in direct contact with the first doped region; and

a second doped region of the first conductive type and <u>a</u> third doped region of the second conductive type located within the second well region and adjacent to the surface of the substrate, wherein the third doped region and the second doped region are <u>each heavily doped and are not physically contacted in direct contact</u> with each other.

wherein shallow trench isolations regions are formed adjacent to the surface of the substrate, so as to respectively separate immediately neighboring regions of said first, second and third regions.

Claim 13. (Currently Amended) The diode string structure of claim 12, wherein for each of additional diode structures between neither the starting diode structure ner and the ending diode structure in the diode string, there is a post diode structure in the diode string structure directly located next to said each of the additional the diode structures, and the third doped region of said each of the additional the diode structures is coupled to the second doped region of the post diode structure.

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Claim 14. (Currently Amended) The diode string structure of claim 13, wherein for the starting diode structure, the second doped region of the starting diode structure is coupled to the first doped region and the third doped region of the starting diode structure is coupled to the second doped region of another one of the additional diode structures next to the starting diode structure in the diode string structure.

Claim 15. (Currently Amended) The diode string structure of claim 13, wherein for the ending diode structure, the third doped region of the ending diode structure is coupled to a ground terminal and the second doped region of the ending diode structure is coupled to the third doped region of another one of the additional diode structures prior to immediately before the ending diode structure in the diode string structure.

Claims 16-17. (Cancelled)

Claim 18. (Currently Amended) The diode string structure of claim 12, wherein the first conductive type is a p-doped type and the second conductive type is an n-doped type, or the first conductive type is an n-doped type and the second conductive type is a p-doped type.

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Allowable Subject Matter

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Claims 12-15 and 18 are allowed.

Conclusion

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Shouxiang Hu whose telephone number is 571-272-

1654. The examiner can normally be reached on Monday through Thursday, 7:30 AM

to 6:00 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Eddie C. Lee can be reached on 571-272-1732. The fax phone number for

the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the

Patent Application Information Retrieval (PAIR) system. Status information for

published applications may be obtained from either Private PAIR or Public PAIR.

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June 21, 2005